Microsemi Corporation - A1240A-1PLG84C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	684
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	72
Number of Gates	4000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	84-LCC (J-Lead)
Supplier Device Package	84-PLCC (29.31x29.31)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1240a-1plg84c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Table 2-1 • **Absolute Maximum Ratings**[1]

Symbol	Parameter	Limits	Units
VCC	DC supply voltage	–0.5 to +7.0	V
VI	Input voltage	–0.5 to VCC + 0.5	V
VO	Output voltage	–0.5 to VCC + 0.5	V
IIO	I/O source sink current[2]	±20	mA
T_{STG}	Storage temperature	–65 to +150	°C

Notes:

1. *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the recommended operating conditions.*
2. *Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than VCC + 0.5 V for less than GND –0.5 V, the internal protection diodes will be forward biased and can draw excessive current.*

Table 2-2 • **Recommended Operating Conditions**

Parameter	Commercial	Industrial	Military	Units
Temperature range*	0 to +70	–40 to +85	–55 to +125	°C
Power supply tolerance	±5	±10	±10	%VCC

*Note: *Ambient temperature (T_A) is used for commercial and industrial; case temperature (T_C) is used for military.*

Table 2-3 • Electrical Specifications

Symbol	Parameter	Commercial		Industrial		Military		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
VOH[1]	(IOH = –10 mA)[2]	2.4	–	–	–	–	–	V
	(IOH = –6 mA)	3.84	–	–	–	–	–	V
	(IOH = –4 mA)	–	–	3.7	–	3.7	–	V
VOL[1]	(IOL = 10 mA)[2]	–	0.5	–	–	–	–	V
	(IOL = 6 mA)	–	0.33	–	0.40	–	0.40	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
Input Transition Time t_R, t_F[2]		–	500	–	500	–	500	ns
C_{IO} I/O capacitance[2,3]		–	10	–	10	–	10	pF
Standby Current, ICC[4] (typical = 1 mA)		–	2	–	10	–	20	mA
Leakage Current[5]		–10	+10	–10	+10	–10	+10	µA
ICC(D)	Dynamic VCC supply current. See the Power Dissipation section.							

Notes:

1. *Only one output tested at a time. VCC = minimum.*
2. *Not tested, for information only.*
3. *Includes worst-case PG176 package capacitance. VOUT = 0 V, f = 1 MHz*
4. *All outputs unloaded. All inputs = VCC or GND, typical ICC = 1 mA. ICC limit includes IPP and ISV during normal operations.*
5. *VOUT, VIN = VCC or GND.*

Package Thermal Characteristics

The device junction to case thermal characteristic is θjc, and the junction to ambient air characteristic is θja. The thermal characteristics for θja are shown with two different air flow rates.

Maximum junction temperature is 150°C.

A sample calculation of the absolute maximum power dissipation allowed for a PQ160 package at commercial temperature and still air is as follows:

$$\frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}\,\text{°C/W}} = \frac{150\text{°C} - 70\text{°C}}{33\text{°C/W}} = 2.4\ \text{W}$$

EQ 1

Table 2-4 • **Package Thermal Characteristics**

Package Type*	**Pin Count**	θ_{jc}	θ_{ja} **Still Air**	θ_{ja} **300 ft./min.**	**Units**
Ceramic Pin Grid Array	100	5	35	17	°C/W
	132	5	30	15	°C/W
	176	8	23	12	°C/W
Ceramic Quad Flatpack	172	8	25	15	°C/W
Plastic Quad Flatpack[1]	100	13	48	40	°C/W
	144	15	40	32	°C/W
	160	15	38	30	°C/W
Plastic Leaded Chip Carrier	84	12	37	28	°C/W
Very Thin Quad Flatpack	100	12	43	35	°C/W
Thin Quad Flatpack	176	15	32	25	°C/W

Notes: (Maximum Power in Still Air)

1. *Maximum power dissipation values for PQFP packages are 1.9 W (PQ100), 2.3 W (PQ144), and 2.4 W (PQ160).*
2. *Maximum power dissipation for PLCC packages is 2.7 W.*
3. *Maximum power dissipation for VQFP packages is 2.3 W.*
4. *Maximum power dissipation for TQFP packages is 3.1 W.*

Power Dissipation

$$P = [\text{ICC standby} + \text{ICCactive}] * \text{VCC} + \text{IOL} * \text{VOL} * N + \text{IOH} * (\text{VCC} - \text{VOH}) * M$$

EQ 2

where:

ICC standby is the current flowing when no inputs or outputs are changing

ICCactive is the current flowing due to CMOS switching.

IOL and IOH are TTL sink/source currents.

VOL and VOH are TTL level output voltages.

N is the number of outputs driving TTL loads to VOL.

M is the number of outputs driving TTL loads to VOH.

An accurate determination of N and M is problematical because their values depend on the family type, design details, and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-5 for commercial, worst case conditions.

***Table 2-5* • Standby Power Calculation**

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 3.

$$\text{Power } (\mu\text{W}) = C_{EQ} * VCC^2 * F \qquad \textit{EQ 3}$$

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring ICC active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown in Table 2-6.

***Table 2-6* • CEQ Values for Microsemi FPGAs**

Item	CEQ Value
Modules (C_{EQM})	5.8
Input Buffers (C_{EQI})	12.9
Output Buffers (C_{EQO})	23.8
Routed Array Clock Buffer Loads (C_{EQCR})	3.9

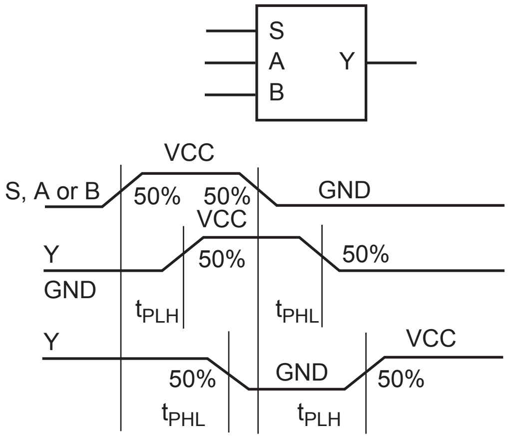
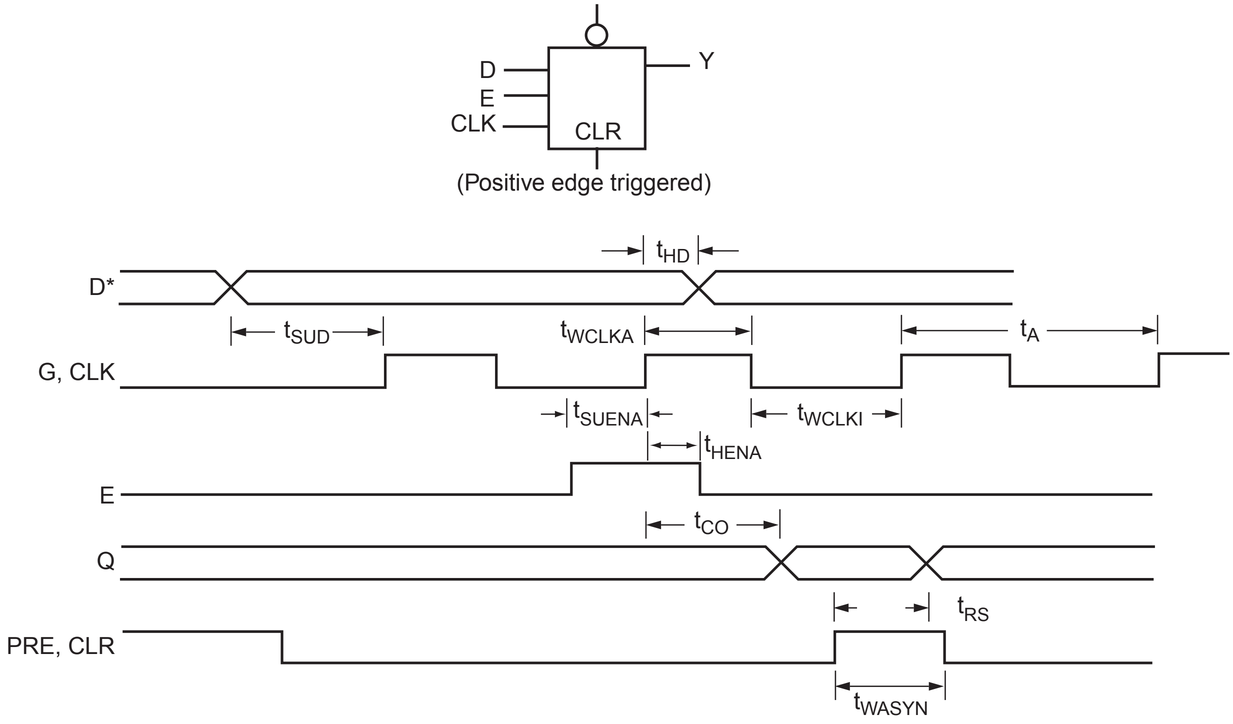


Figure 2-5 • **Module Delays**

Sequential Module Timing Characteristics



Note: D represents all data functions involving A, B, and S for multiplexed flip-flops.

Figure 2-6 • **Flip-Flops and Latches**

A1225A Timing Characteristics (continued)

Table 2-14 **• A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

TTL Output Module Timing[1]		–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{DLH}	Data to Pad High		8.0		9.0		10.6	ns
t_{DHL}	Data to Pad Low		10.1		11.4		13.4	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.07		0.08		0.09	ns/pF
d_{THL}	Delta High to Low		0.12		0.13		0.16	ns/pF
CMOS Output Module Timing[1]								
t_{DLH}	Data to Pad High		10.1		11.5		13.5	ns
t_{DHL}	Data to Pad Low		8.4		9.6		11.2	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.12		0.13		0.16	ns/pF
d_{THL}	Delta High to Low		0.09		0.10		0.12	ns/pF

Notes:

1. *Delays based on 50 pF loading.*
2. *SSO information can be found at www.microsemi.com/soc/techdocs/appnotes/board_consideration.aspx.*

A1280A Timing Characteristics

***Table 2-18* • A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

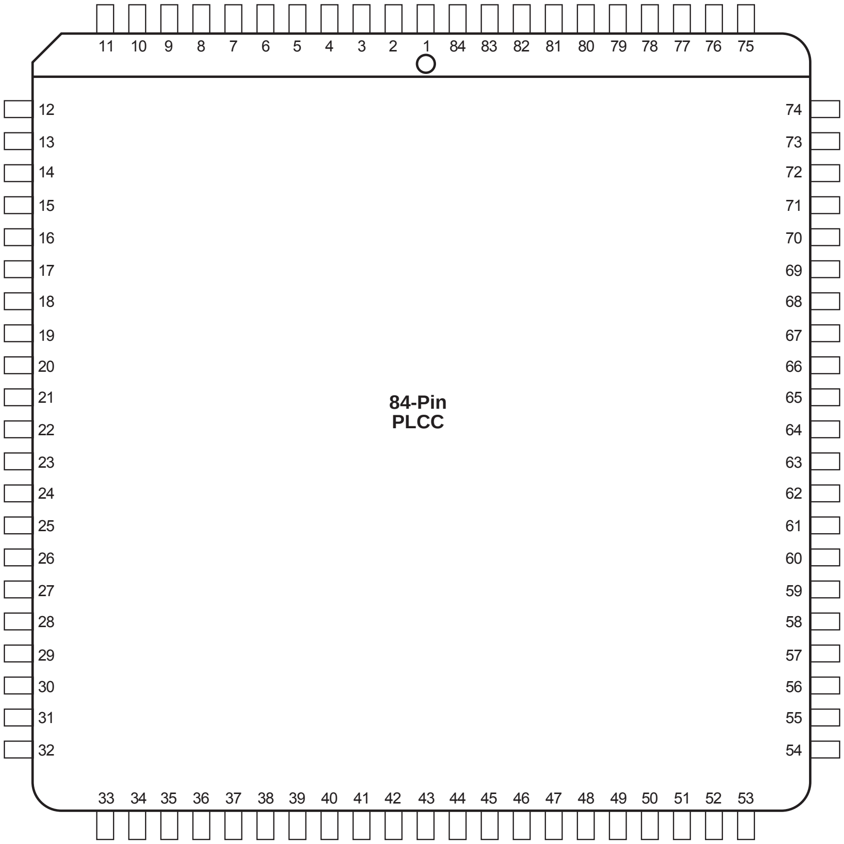
Logic Module Propagation Delays[1]		**–2 Speed**[3]		**–1 Speed**		**Std. Speed**		**Units**
Parameter/Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{PD1}	Single Module		3.8		4.3		5.0	ns
t_{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t_{GO}	Latch G to Q		3.8		4.3		5.0	ns
t_{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays[2]								
t_{RD1}	FO = 1 Routing Delay		1.7		2.0		2.3	ns
t_{RD2}	FO = 2 Routing Delay		2.5		2.8		3.3	ns
t_{RD3}	FO = 3 Routing Delay		3.0		3.4		4.0	ns
t_{RD4}	FO = 4 Routing Delay		3.7		4.2		4.9	ns
t_{RD8}	FO = 8 Routing Delay		6.7		7.5		8.8	ns
Sequential Timing Characteristics[3,4]								
t_{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t_{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t_{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	5.5		6.0		7.0		ns
t_{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	5.5		6.0		7.0		ns
t_A	Flip-Flop Clock Input Period	11.7		13.3		18.0		ns
t_{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t_{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t_{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t_{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f_{MAX}	Flip-Flop (Latch) Clock Frequency		85.0		75.0		50.0	MHz

Notes:

1. *For dual-module macros, use $t_{PD1} + t_{RD1} + t_{PDn}$, $t_{CO} + t_{RD1} + t_{PDn}$, or $t_{PD1} + t_{RD1} + t_{SUD}$—whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*
3. *Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.*
4. *Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.*

3 – Package Pin Assignments

PL84



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

PQ100	
Pin Number	**A1225A Function**
2	DCLK, I/O
4	MODE
9	GND
16	VCC
17	VCC
22	GND
34	GND
40	VCC
46	GND
52	SDO
57	GND
64	GND

PQ100	
Pin Number	**A1225A Function**
65	VCC
66	VCC
67	VCC
72	GND
79	SDI, I/O
84	GND
87	PRA, I/O
89	CLKA, I/O
90	VCC
92	CLKB, I/O
94	PRB, I/O
96	GND

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ160	
Pin Number	**A1280A Function**
2	DCLK, I/O
6	VCC
11	GND
16	PRB, I/O
18	CLKB, I/O
20	VCC
21	CLKA, I/O
23	PRA, I/O
30	GND
35	VCC
38	SDI, I/O
40	GND
44	GND
49	GND
54	VCC
57	VCC
58	VCC
59	GND
60	VCC
61	GND
64	GND

PQ160	
Pin Number	**A1280A Function**
69	GND
80	GND
82	SDO
86	VCC
89	GN
98	GND
99	GND
109	GND
114	VCC
120	GND
125	GND
130	GND
135	VCC
138	VCC
139	VCC
140	GND
145	GND
150	VCC
155	GND
159	MODE
160	GND

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

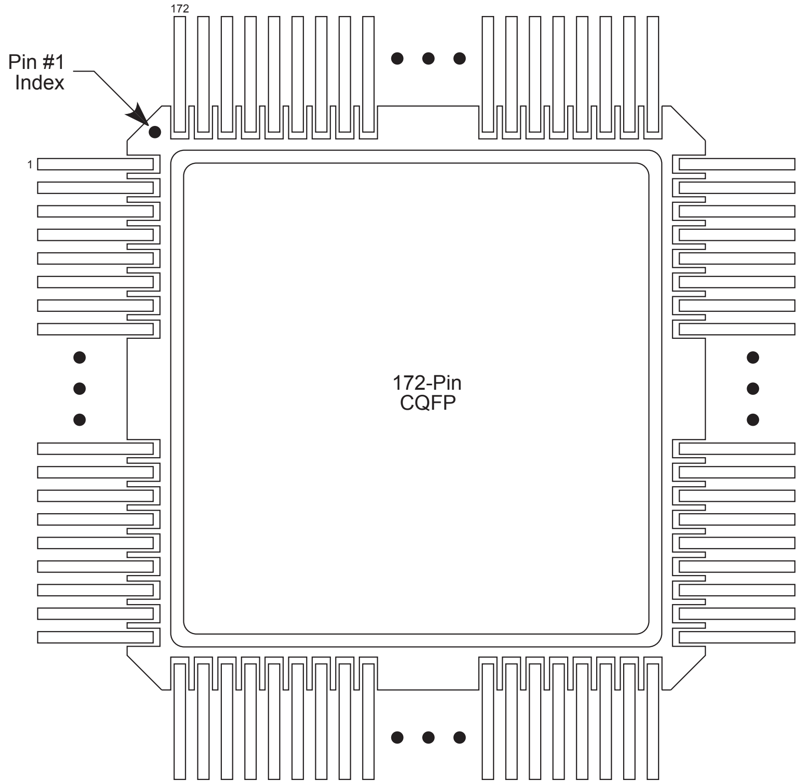
VQ100	
Pin Number	**A1225A Function**
2	MODE
7	GND
14	VCC
15	VCC
20	GND
32	GND
38	VCC
44	GND
50	SDO
55	GND
62	GND
63	VCC

VQ100	
Pin Number	**A1225A Function**
64	VCC
65	VCC
70	GND
77	SDI, I/O
82	GND
85	PRA, I/O
87	CLKA, I/O
88	VCC
90	CLKB, I/O
92	PRB, I/O
94	GND
100	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

CQ172



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx

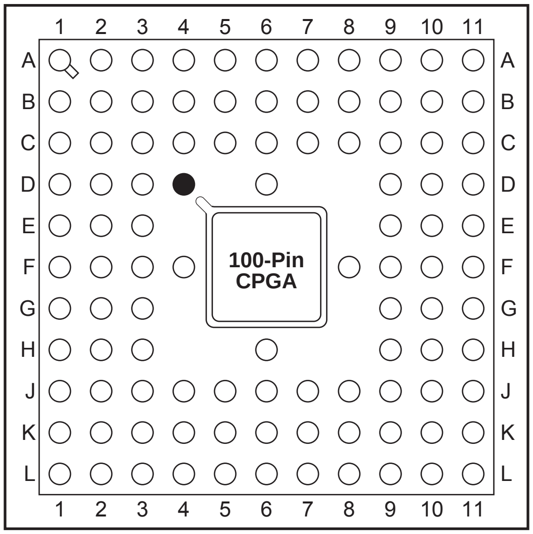
CQ172	
Pin Number	**A1280A Function**
1	MODE
7	GND
12	VCC
17	GND
22	GND
23	VCC
24	VCC
27	VCC
32	GND
37	GND
50	VCC
55	GND
65	GND
66	VCC
75	GND
80	VCC
85	SDO
98	GND
103	GND
106	GND

CQ172	
Pin Number	**A1280A Function**
107	VCC
108	GND
109	VCC
110	VCC
113	VCC
118	GND
123	GND
131	SDI, I/O
136	VCC
141	GND
148	PRA, I/O
150	CLKA, I/O
151	VCC
152	GND
154	CLKB, I/O
156	PRB, I/O
161	GND
166	VCC
171	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG100

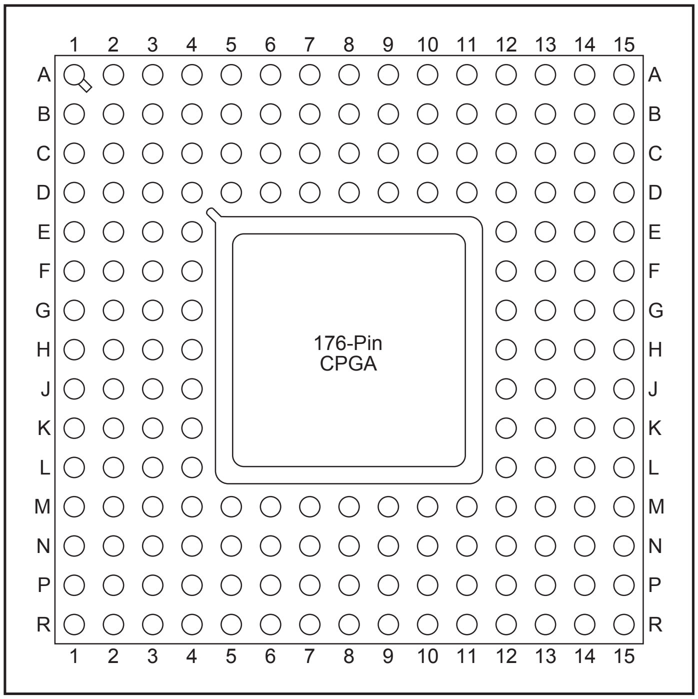


● Orientation Pin

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx

PG176



Note

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4 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the datasheet.

Revision	Changes	Page
Revision 8 (January 2012)	The ACT 2 datasheet was formatted newly in the style used for current datasheets. The same information is present (other than noted in the list of changes for this revision) but divided into chapters.	N/A
	Package names used in Table 1 • ACT 2 Product Family Profile and throughout the document were revised to match standards given in *Package Mechanical Drawings* (SAR 27395).	I
	The description for SDO pins had earlier been removed from the datasheet and has now been included again, in the "Pin Descriptions" section (SAR 35819).	2-21
	SDO pin numbers had earlier been removed from package pin assignment tables in the datasheet, and have now been restored to the pin tables (SAR 35819).	3-2
Revision 7 (June 2006)	The "Ordering Information" section was revised to include RoHS information.	II
Revision 6 (December 2000)	In the "PG176" package, pin A3 was incorrectly assigned as CLKA, I/O. A3 is a user I/O. Pin A9 is CLKA, I/O.	3-21

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